

2SD1119

Silicon NPN epitaxial planer type

For low-frequency power amplification

■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Satisfactory operation performances at high efficiency with the low-voltage power supply.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	40	V
Collector to emitter voltage	V_{CEO}	25	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	5	A
Collector current	I_C	3	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

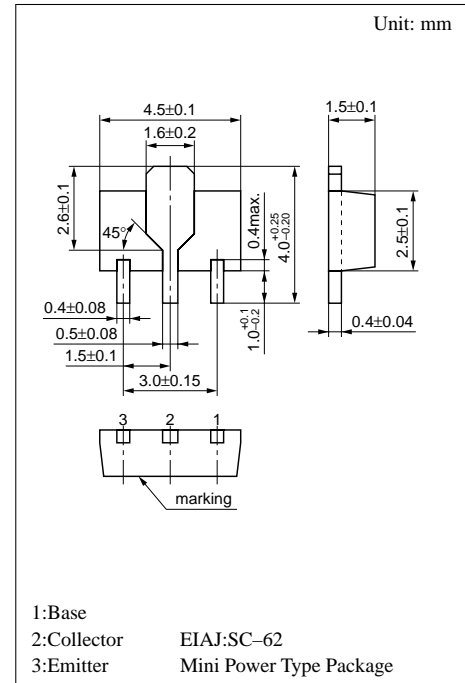
■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 10V, I_E = 0$			0.1	μA
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	25			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = 2V, I_C = 0.5A^{*2}$	230		600	
	h_{FE2}	$V_{CE} = 2V, I_C = 2A^{*2}$	150			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 0.1A^{*2}$			1	V
Transition frequency	f_T	$V_{CB} = 6V, I_E = -50mA, f = 200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 20V, I_E = 0, f = 1MHz$			50	pF

*2 Pulse measurement

*1 h_{FE1} Rank classification

Rank	Q	R
h_{FE1}	230 ~ 380	340 ~ 600
Marking Symbol	TQ	TR



Marking symbol : T

